



60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
2014	17mΩ @ V _{GS} = 10V	46.9A
60V	24mΩ @ V _{GS} = 4.5V	38.3A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Power Management Functions
- DC-DC Converters
- Backlighting

Features

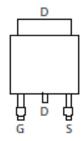
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Ensures On State Losses Are Minimized
- Excellent Q_{gd} x R_{DS(ON)} Product (FOM)
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

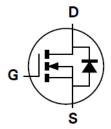
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.33 grams (Approximate)



Top View



Pin Out Top View



Equivalent Circuit

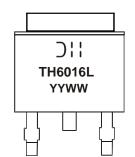
Ordering Information (Note 5)

Part Number	Case	Packaging
DMTH6016LK3Q-13	TO252 (DPAK)	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Please refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



Oll = Manufacturer's Marking
TH6016L = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 18 = 2018)
WW = Week Code (01 to 53)

April 2018



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	60	V	
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	$T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$	I _D	10.8 7.6	А
Continuous Drain Current (Note 7) V _{GS} = 10V	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I _D	46.9 33.2	А
Maximum Continuous Body Diode Forward Current (Note 7)	Is	50	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	70	Α	
Avalanche Current, L = 0.1mH		I _{AS}	15.3	Α
Avalanche Energy, L = 0.1mH	E _{AS}	11.7	mJ	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P _D	3.2	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ heta JA}$	47	°C/W
Total Power Dissipation (Note 7)	P_{D}	60	W
Thermal Resistance, Junction to Case (Note 7)	$R_{ heta JC}$	2.5	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

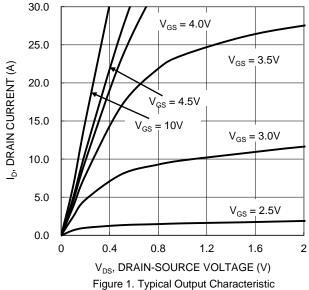
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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)		1				T	
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	1	_	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	D		11	17	mΩ	$V_{GS} = 10V, I_D = 10A$	
Static Diani-Source On-Nesistance	R _{DS(ON)}	_	16	24	mΩ	$V_{GS} = 4.5V, I_D = 6A$	
Diode Forward Voltage	V_{SD}		0.9	1.2	V	$V_{GS} = 0V$, $I_S = 1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss		864	_		$V_{DS} = 30V$, $V_{GS} = 0V$, $f = 1MHz$	
Output Capacitance	Coss		282	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	27.1	_			
Gate Resistance	R_{g}	_	1.35	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg	_	17	_		V _{DS} = 30V, I _D = 10A	
Total Gate Charge (V _{GS} = 4.5V)	Qg		8.4	_	nC		
Gate-Source Charge	Q_{gs}	_	3.1	_	110		
Gate-Drain Charge	Q_{gd}	_	4.3	_			
Turn-On Delay Time	t _{D(ON)}	_	3.4	_		$V_{DD} = 30V, V_{GS} = 10V,$ $R_G = 6\Omega, I_D = 10A$	
Turn-On Rise Time	t _R	_	5.2	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	12.9	_	115		
Turn-Off Fall Time	t _F	_	6.8	_			
Body Diode Reverse Recovery Time	t _{RR}	_	22	_	ns	1 100 1:/14 1000///	
Body Diode Reverse Recovery Charge	Q_{RR}	_	11.1	_	$\frac{1}{nC}$ I _F = 10A, di/dt = 400A/µs		

^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
7. Device mounted on infinite heat sink and measured by thermal couple attached on bottom heat sink of package.

^{8.} Short duration pulse test used to minimize self-heating effect.

^{9.} Guaranteed by design. Not subject to product testing.





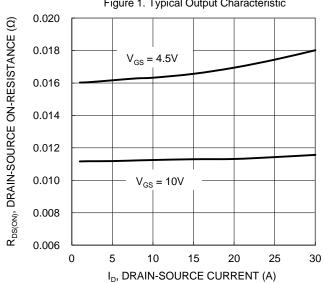


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

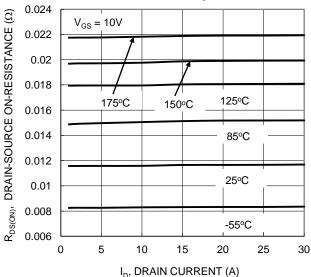


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

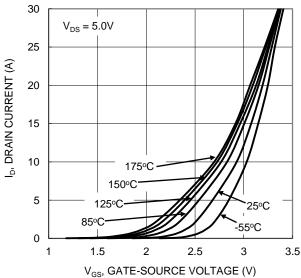


Figure 2. Typical Transfer Characteristic

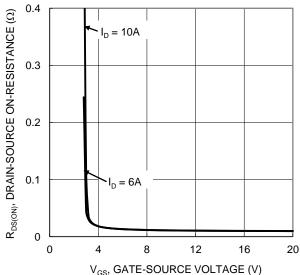


Figure 4. Typical Transfer Characteristic

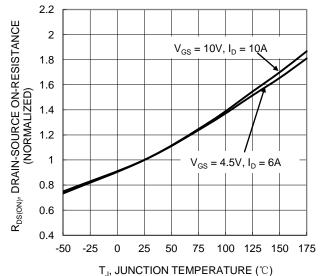
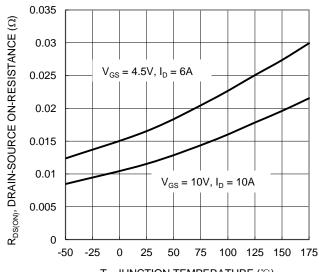


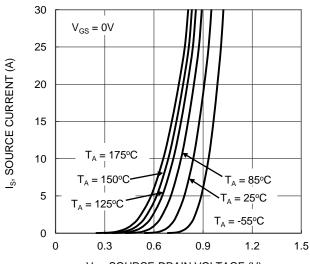
Figure 6. On-Resistance Variation with Temperature



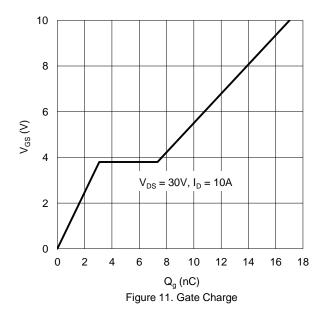




 $\rm T_J, JUNCTION$ TEMPERATURE (°C) Figure 7. On-Resistance Variation with Temperature



V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current



 $V_{GS(TH)}$, GATE THRESHOLD VOLTAGE (V) 1.8 1.6 $I_D = 1 \text{mA}$ 1.4 1.2 $I_D = 250 \mu A$ 1 0.8 0.6 0.4 -50 -25 25 50 75 100 125 150 175

2

 T_J , JUNCTION TEMPERATURE ($^{\circ}$ C) Figure 8. Gate Threshold Variation vs. Temperature

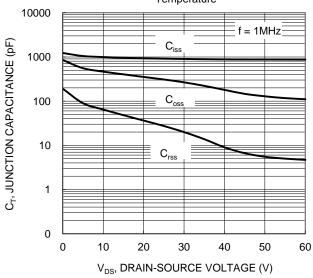
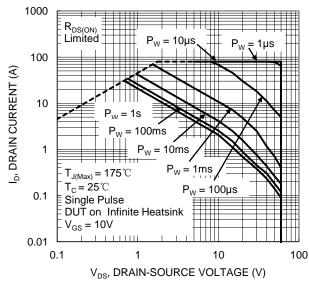


Figure 10. Typical Junction Capacitance



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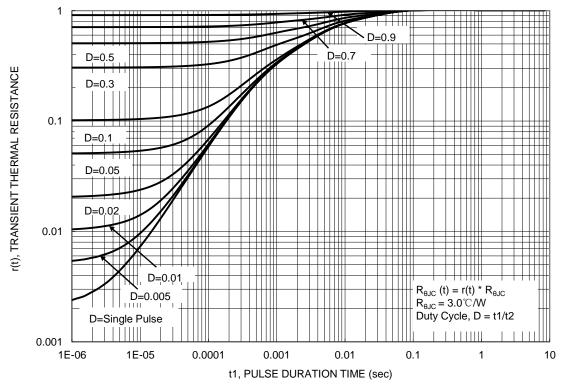


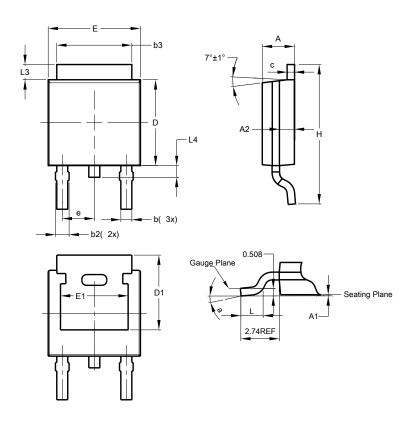
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

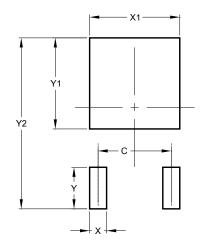


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
С	4.572
Х	1.060
X1	5.632
Υ	2.600
Y1	5.700
Y2	10.700



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